

TSP12N65M/TSF12N65M

650V N-Channel MOSFET

General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

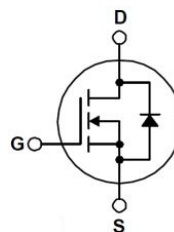
- 12A,650V,Max. $R_{DS(on)}=0.75\ \Omega$ @ $V_{GS}=10V$
- Low gate charge(typical 52nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220



TO-220F



Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter		TSP12N65M	TSF12N65M	Units
V _{DSS}	Drain-Source Voltage		650		V
V _{GS}	Gate-Source Voltage		± 30		V
I _D	Drain Current	T _C = 25°C	12	12*	A
		T _C = 100°C	7.4	7.4*	A
I _{DM}	Pulsed Drain Current	(Note 1)	48	48*	A
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	865		mJ
I _{AR}	Avalanche Current	(Note 1)	12		A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	23.1		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C)		231	54	W
	-Derate above 25°C		1.85	0.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	TSP12N65M	TSF12N65M	Units
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case	0.54	2.33	$^{\circ}C/W$
$R_{\theta CS}$	Thermal Resistance,Case-to-Sink Typ.	0.5	--	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient	62.5	62.5	$^{\circ}C/W$

Electrical Characteristics $T_C=25\text{ }^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	--	0.63	0.75	Ω

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to $25\text{ }^{\circ}\text{C}$	--	0.7	--	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 520\text{ V}, T_J = 125^{\circ}\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1850	--	pF
C_{oss}	Output Capacitance		--	180	--	pF
C_{rss}	Reverse Transfer Capacitance		--	20	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 325\text{ V}, I_D = 12\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4,5)	--	30	--	ns
t_r	Turn-On Rise Time		--	90	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	140	--	ns
t_f	Turn-Off Fall Time		--	90	--	ns
Q_g	Total Gate Charge	$V_{DS} = 520\text{ V}, I_D = 12\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4,5)	--	52	--	nC
Q_{gs}	Gate-Source Charge		--	8.5	--	nC
Q_{gd}	Gate-Drain Charge		--	20	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I _S	Continuous Source-Drain Diode Forward Current		--	--	12	A
I _{SM}	Pulsed Source-Drain Diode Forward Current		--	--	48	
V _{SD}	Source-Drain Diode Forward Voltage	I _S = 12 A, V _{GS} = 0 V	--	--	1.4	V
t _{rr}	Reverse Recovery Time	I _S = 12A, V _{GS} = 0 V di _F /dt = 100 A/μs (Note 4)	--	430	--	ns
Q _{rr}	Reverse Recovery Charge		--	5.0	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=11\text{ mH}, I_{AS}=12\text{ A}, V_{DD}=50\text{ V}, R_G=25\text{ }\Omega$, Starting $T_J=25\text{ }^{\circ}\text{C}$
3. $I_{SD}\leq 12\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25\text{ }^{\circ}\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

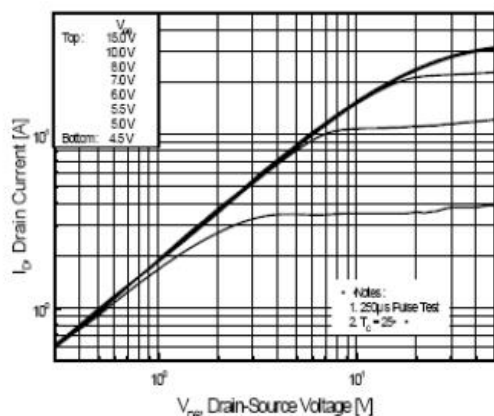


Figure 1. On-Region Characteristics

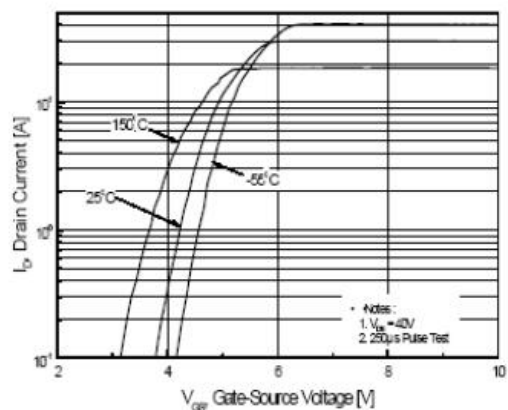


Figure 2. Transfer Characteristics

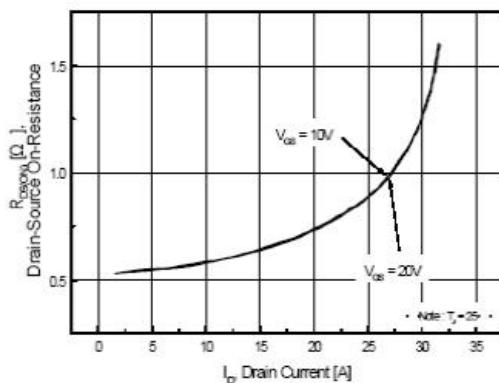


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

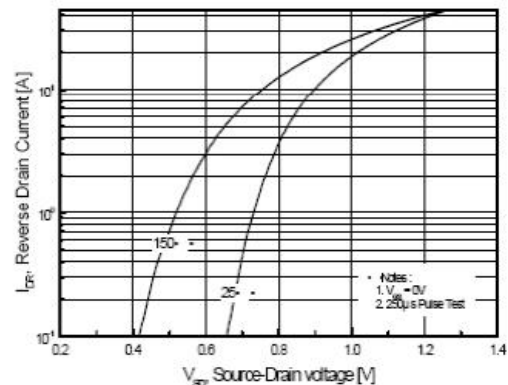


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

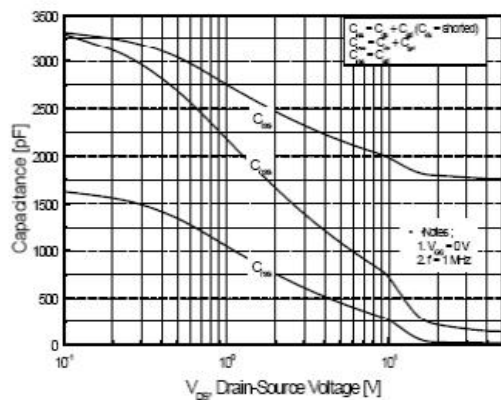


Figure 5. Capacitance Characteristics

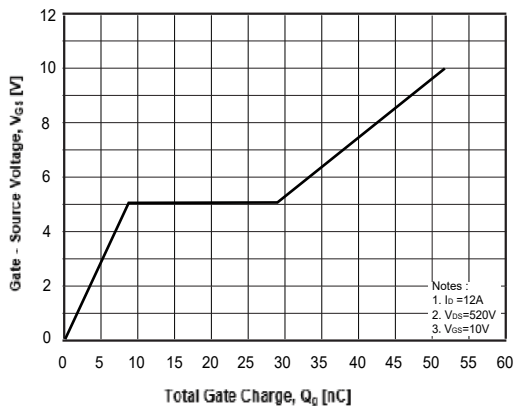


Figure 6. Gate Charge Characteristics

Typical Characteristics

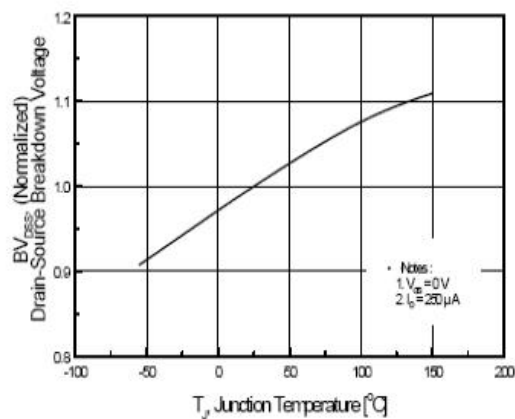


Figure 7. Breakdown Voltage Variation vs Temperature

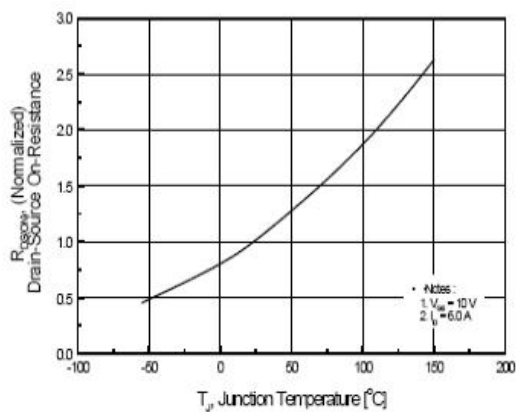


Figure 8. On-Resistance Variation vs Temperature

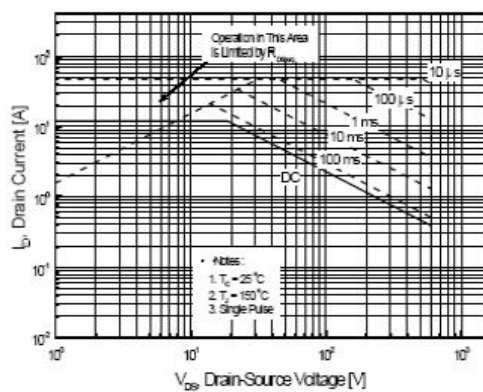


Figure 9-1. Maximum Safe Operating Area for TSP12N65M

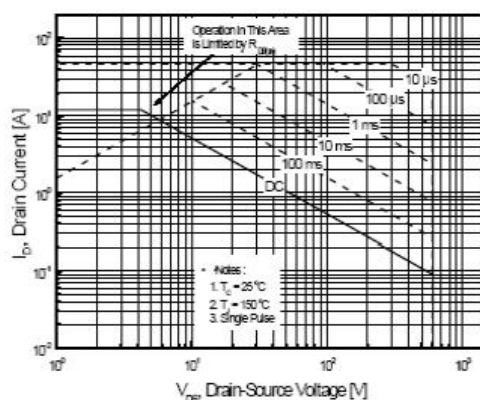


Figure 9-2. Maximum Safe Operating Area for TSF12N65M

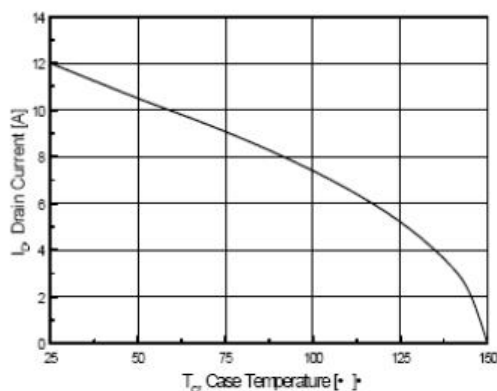


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics

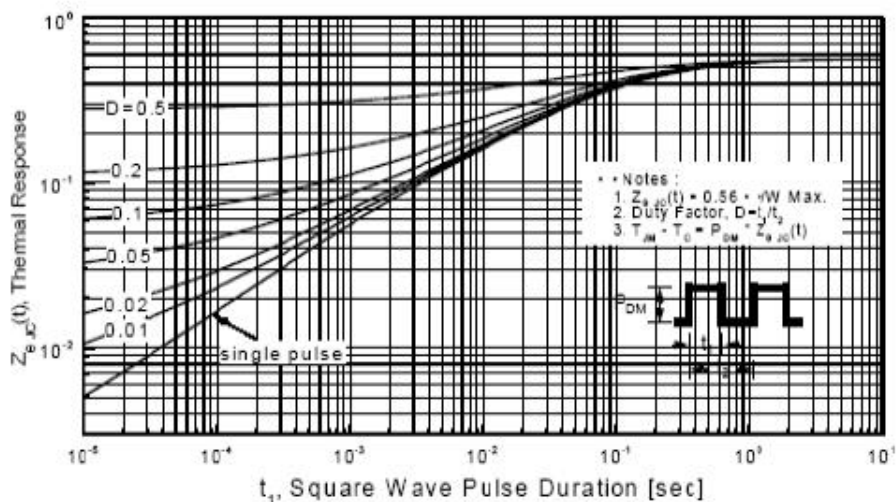


Figure 11-1. Transient Thermal Response Curve
for TSP12N65M

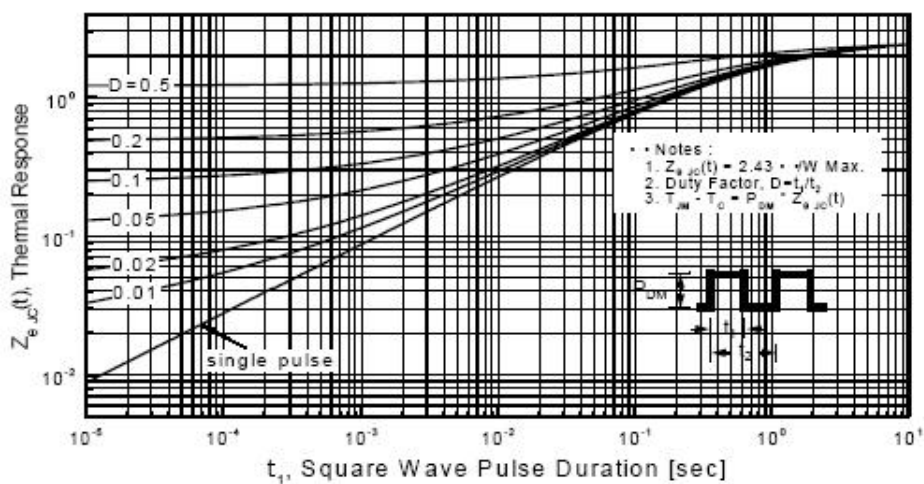


Figure 11-2. Transient Thermal Response Curve
for TSF12N65M

Fig 12. Gate Charge Test Circuit & Waveform

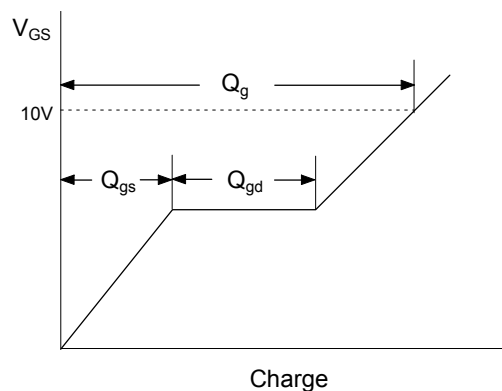
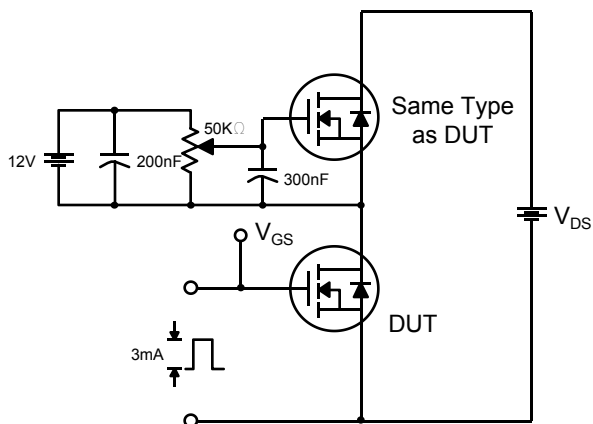


Fig 13. Resistive Switching Test Circuit & Waveforms

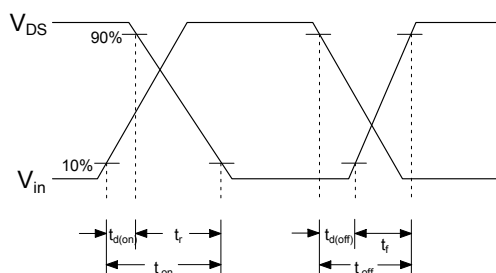
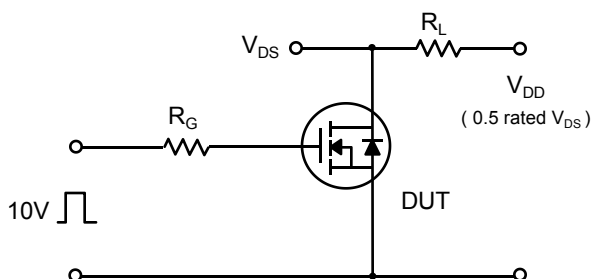


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

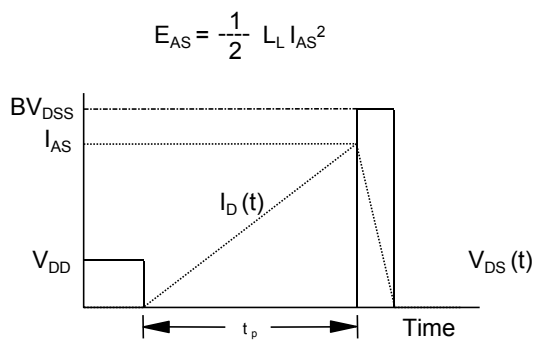
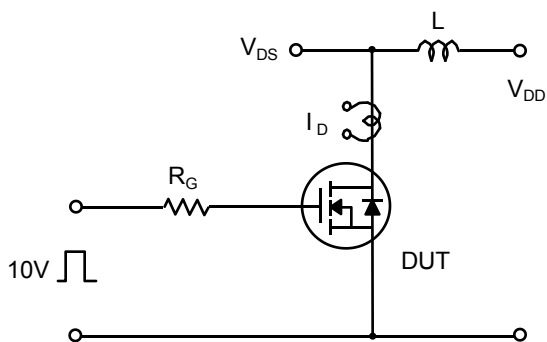


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

